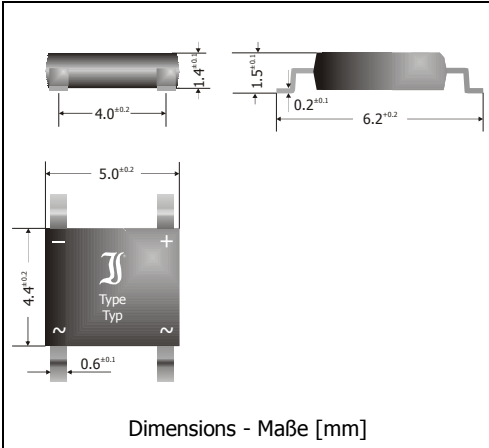


ABS2 ... ABS10
Surface Mount Si-Bridge-Rectifiers with 4mm Pitch
Si-Brückengleichrichter für die Oberflächenmontage mit 4mm Raster

Version 2013-06-19



| | |
|---|---|
| Nominal current – Nennstrom | 0.8 A |
| Alternating input voltage Eingangswechselspannung | 140...700 V |
| Plastic case Kunststoffgehäuse | ABS |
| Weight approx. Gewicht ca. | 0.1 g |
| Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert | Green Molding Halogen-Free |
| Standard packaging taped and reeled Standard Lieferform gegurtet auf Rolle | |

Maximum ratings and Characteristics

| Type Typ | Max. altern. input voltage Max. Eingangswechselspg. | Rep. peak reverse voltage Periodische Spitzensperrepg. |
|-------------|--|---|
| | V_{VRMS} [V] | V_{RRM} [V] ¹⁾ |
| ABS2 | 140 | 200 |
| ABS4 | 280 | 400 |
| ABS6 | 420 | 600 |
| ABS8 | 560 | 800 |
| ABS10 | 700 | 1000 |

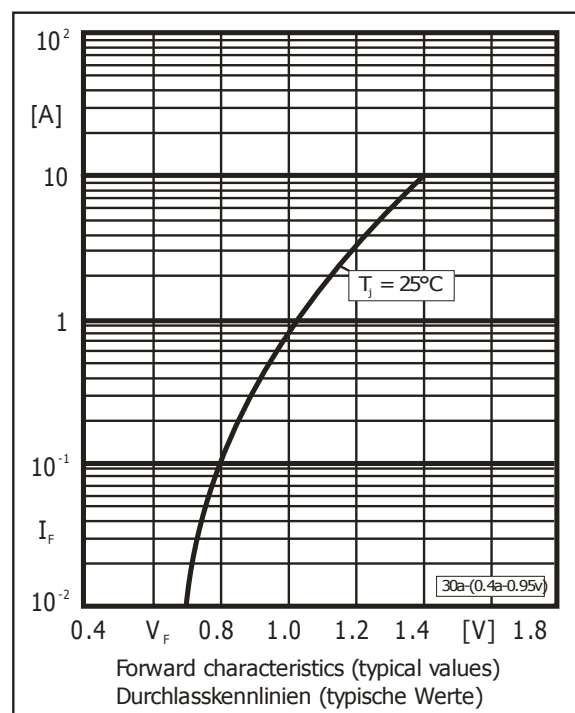
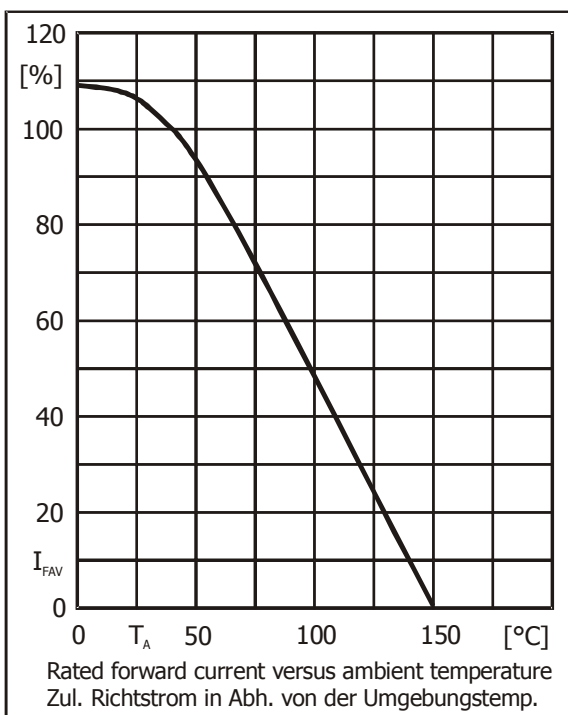
| | | | |
|--|--------------------------|----------------|------------------------------|
| Repetitive peak forward current Periodischer Spitzenstrom | $f > 15$ Hz | I_{FRM} | 5.4 A ²⁾ |
| Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwellen | $T_A = 25^\circ\text{C}$ | I_{FSM} | 27/30 A |
| Rating for fusing, $t < 10$ ms Grenzlastintegral, $t < 10$ ms | $T_A = 25^\circ\text{C}$ | i^2t | 3.6 A ² s |
| Operating junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur | | T_j T_s | -50...+150°C -50...+150°C |

1 Valid per diode – Gültig pro Diode

2 Max. temperature of the terminals $T_T = 100^\circ\text{C}$ – Max. Temperatur der Anschlüsse $T_T = 100^\circ\text{C}$

Characteristics
Kennwerte

| | | | | |
|---|--------------------------|--|------------------------|--|
| Max. average forward rectified current Dauergrenzstrom | $T_A = 40^\circ\text{C}$ | | I_{FAV} I_{FAV} | $0.8 \text{ A}^1)$ $1 \text{ A}^2)$ |
| Forward voltage – Durchlass-Spannung | $T_j = 25^\circ\text{C}$ | $I_F = 0.4 \text{ A}$ $I_F = 0.8 \text{ A}$ | V_F V_F | $< 0.95 \text{ V}^3)$ $< 1.1 \text{ V}^3)$ |
| Leakage current – Sperrstrom | $T_j = 25^\circ\text{C}$ | $V_R = V_{RRM}$ | I_R | $< 5 \mu\text{A}$ |
| Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft | | | R_{thA} R_{thA} | $< 80 \text{ K/W}^1)$ $< 62 \text{ K/W}^2)$ |
| Thermal resistance junction to terminal Wärmewiderstand Sperrschicht – Anschluss | | | R_{thT} | $< 25 \text{ K/W}$ |



- 1 Mounted on P.C. Board with 25 mm^2 copper pads at each terminal
Montage auf Leiterplatte mit 25 mm^2 Kupferbelag (Lötpad) an jedem Anschluss
- 2 Mounted on Alumina Substrate 2500 mm^2 with 1 mm^2 copper pads at each terminal
Montage auf Aluminium-Substrat 2500 mm^2 mit 1 mm^2 Kupferbelag (Lötpad) an jedem Anschluss
- 3 Valid per diode – Gültig pro Diode